

# MCC092 Lab 1 review

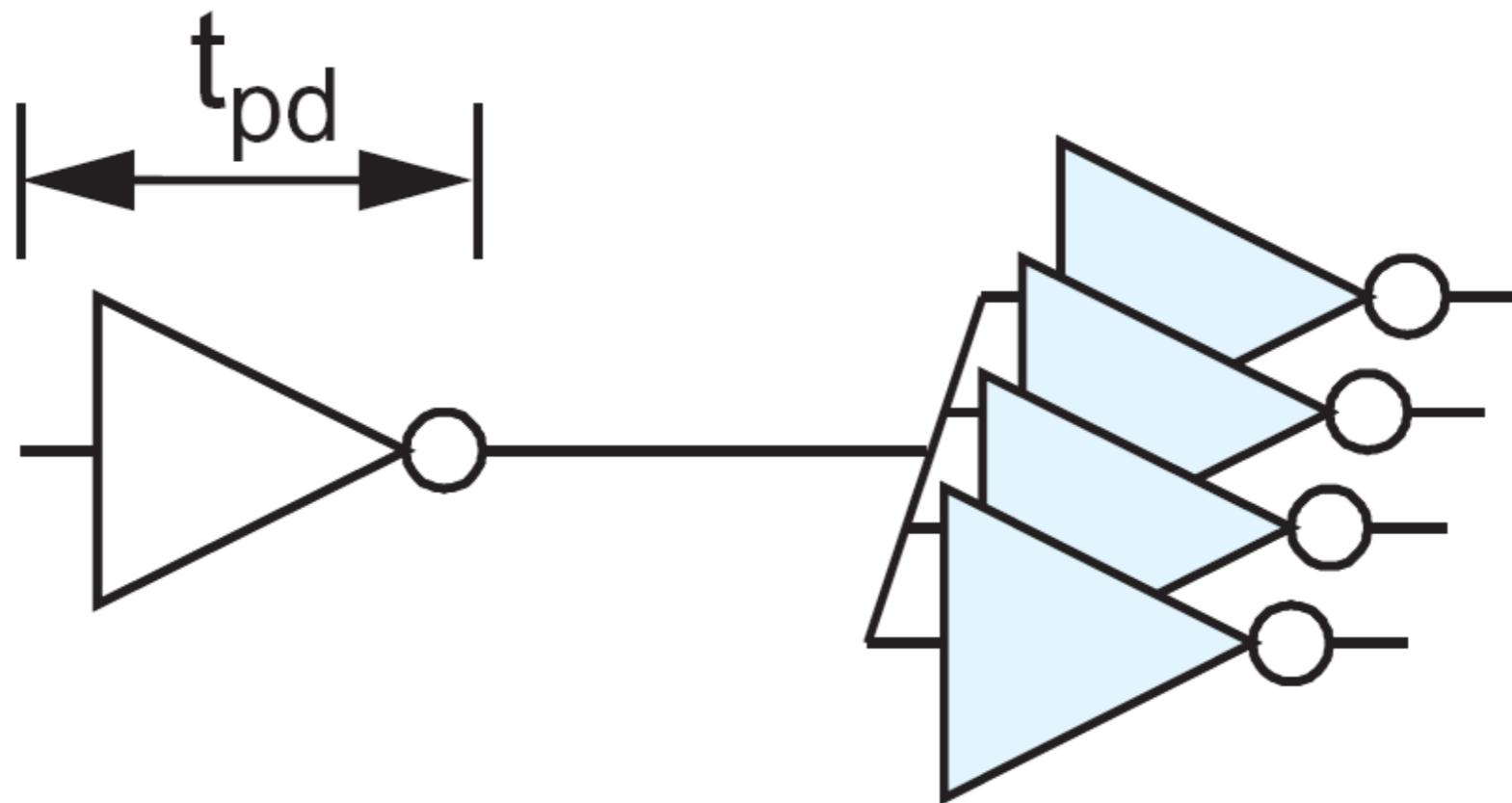
Lena Peterson

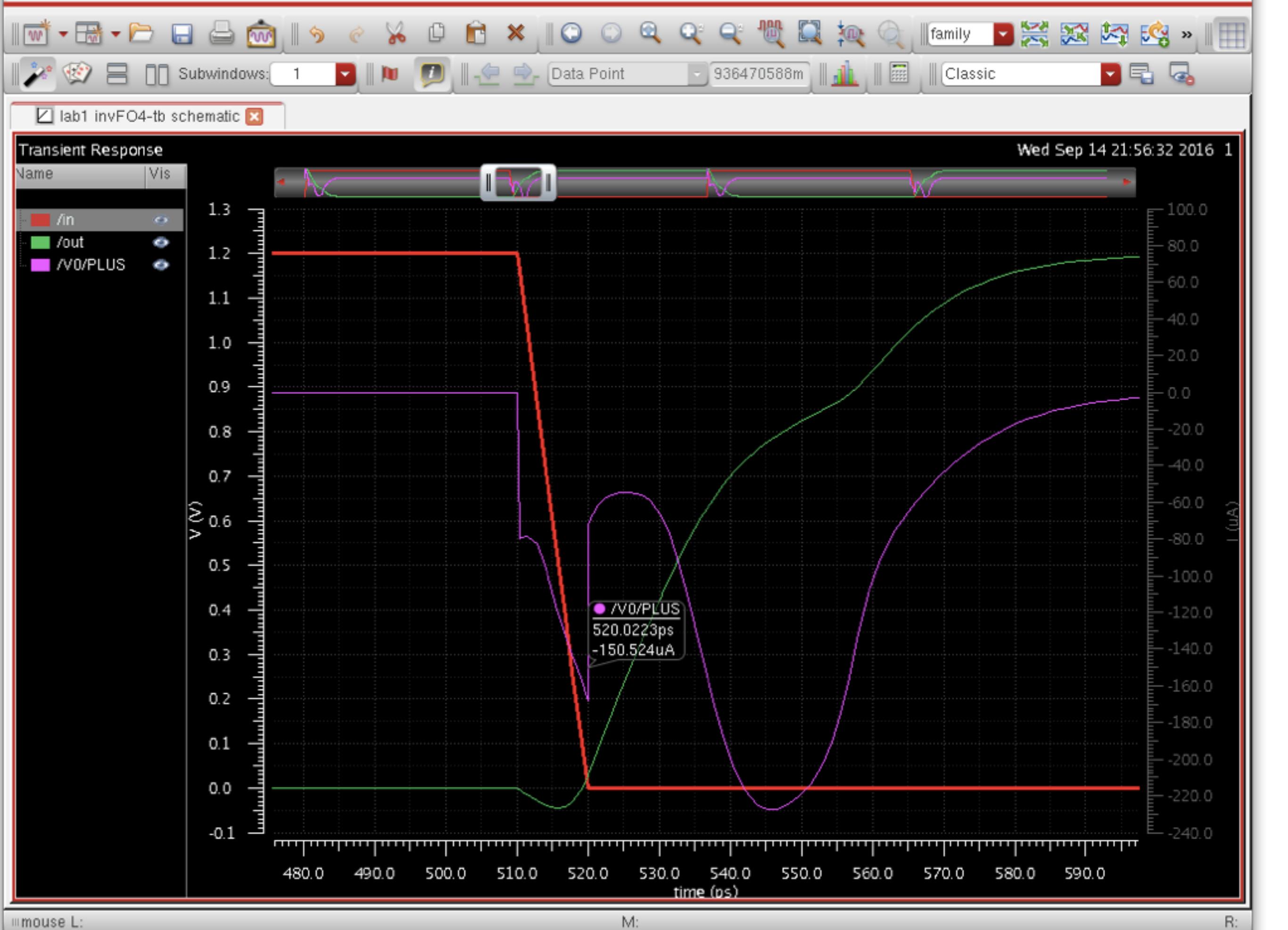
2018-09-18

# Content

- Inverter schematic and cell
- Dynamic: FO4 propagation delay
  - Rise and fall time
  - Rise and fall delays
- Static
  - Switching voltage
  - Noise margins
- Extras

# Why did the FO4 $V_{DD}$ current look so strange?

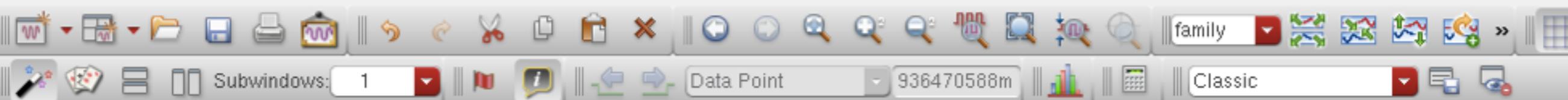




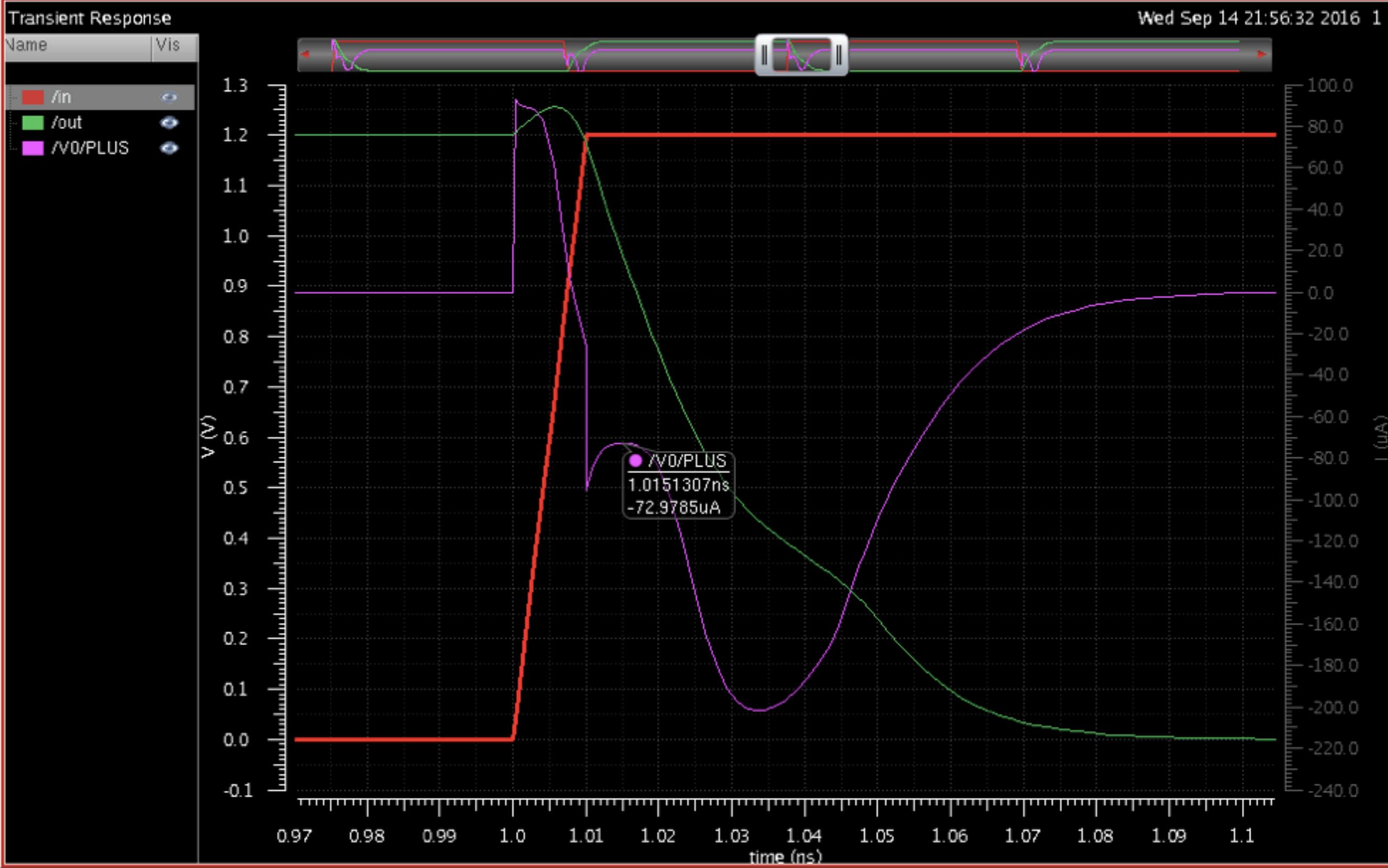
mouse L:

M:

R:

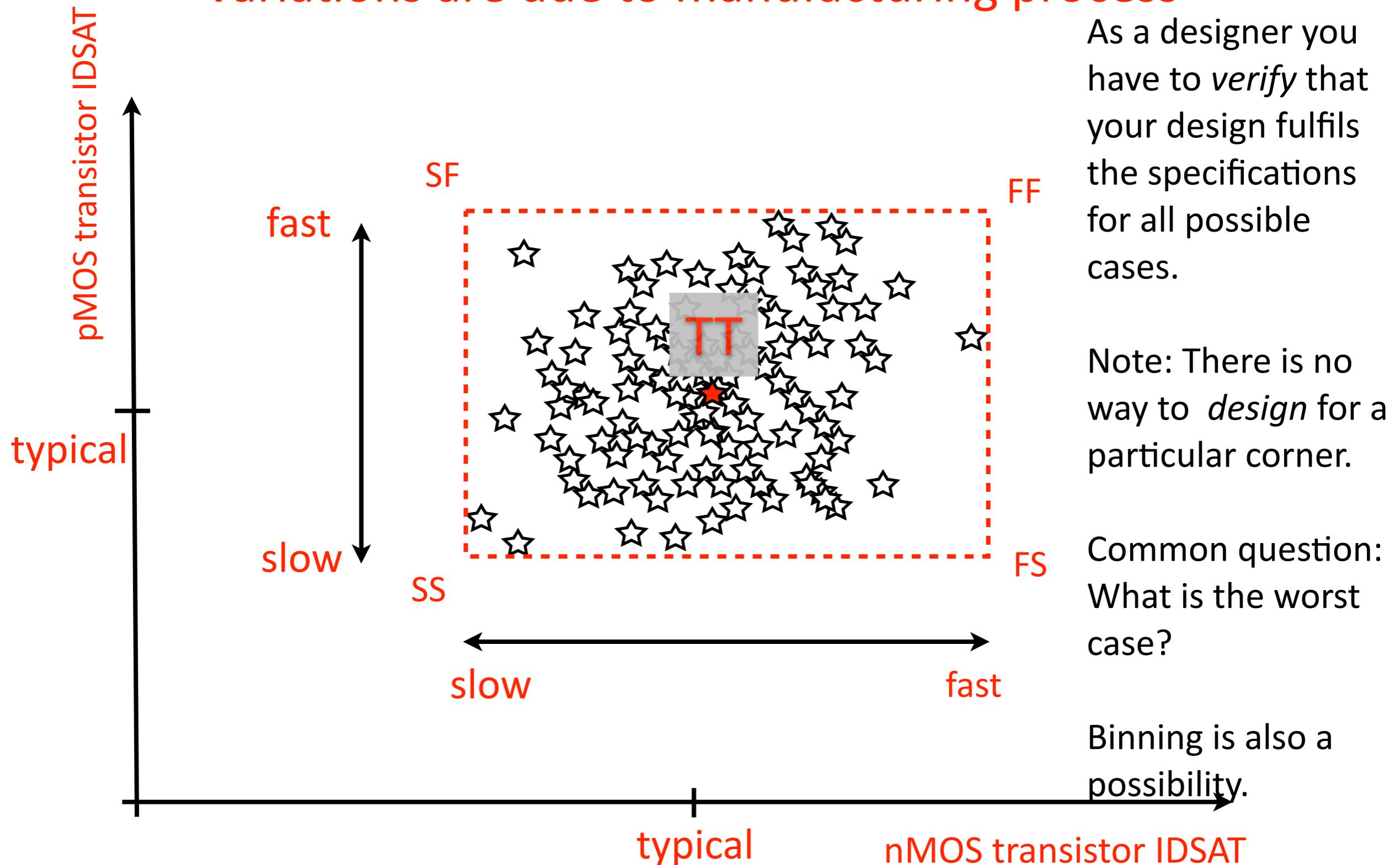


## lab1 invFO4-tb schematic

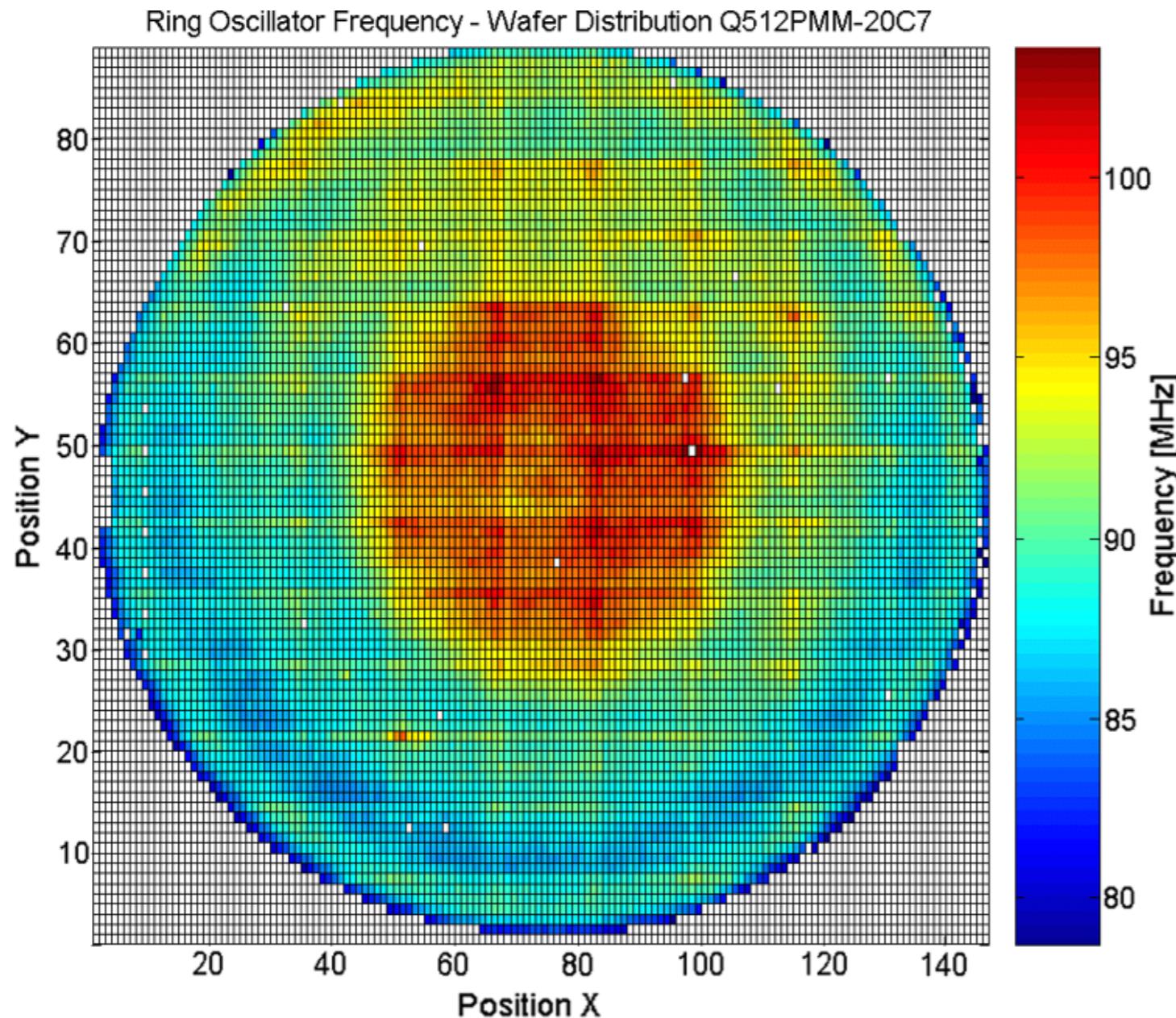


# What are process corners?

Variations are due to manufacturing process



# Binning

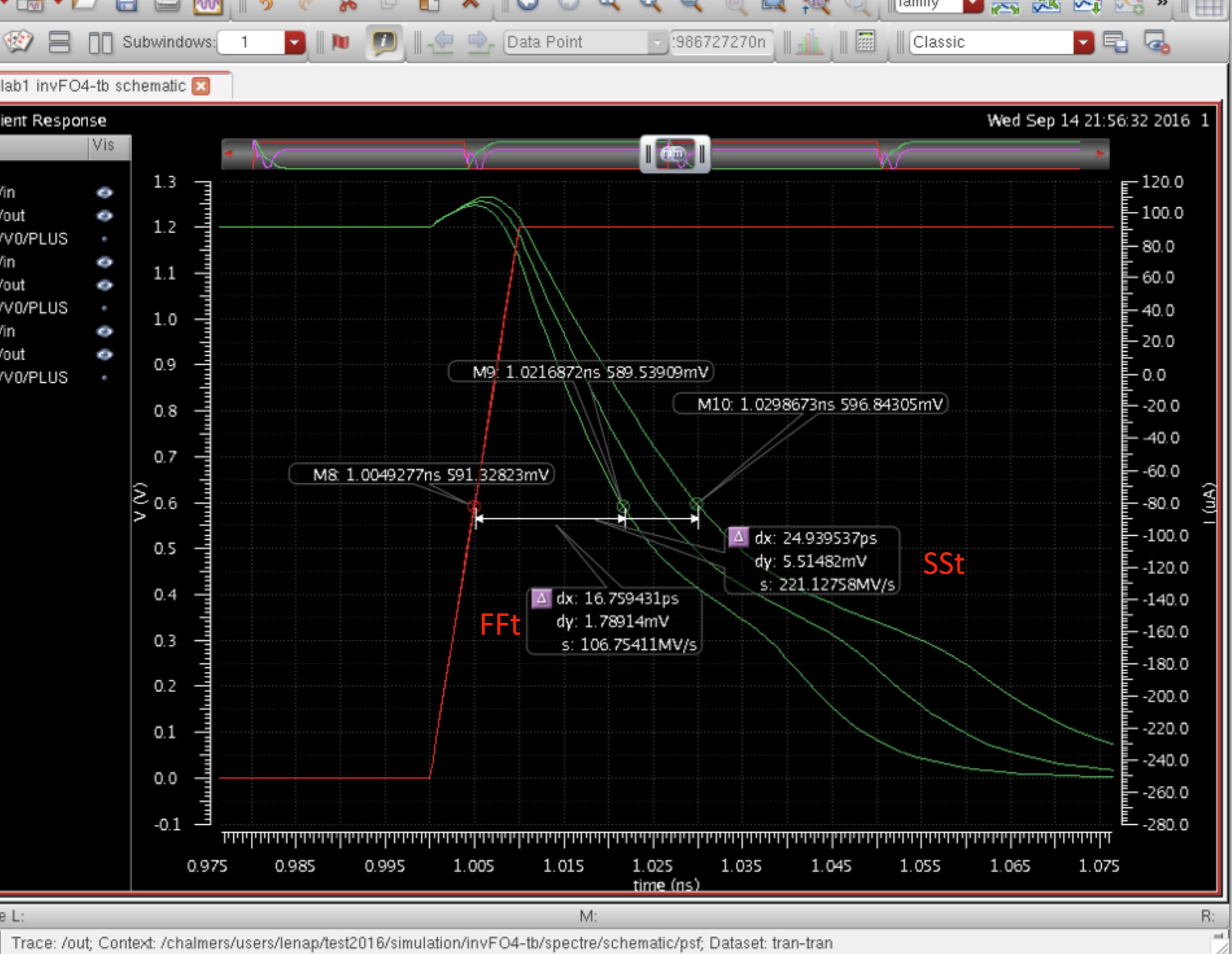


## **Variability:**

The exact same chip may differ in speed due to variability in manufacturing process.

## **Binning:**

Test chips and sort them according to speed.  
Charge more for faster ones.



e L:

M:

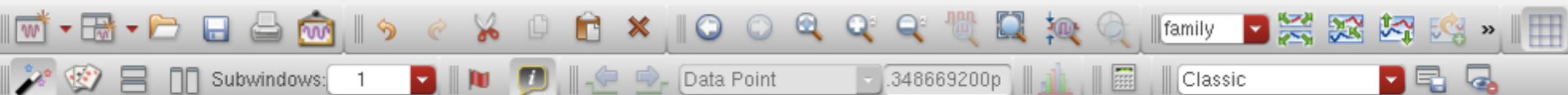
R:

Trace: /out; Context: /chalmers/users/lenap/test2016/simulation/invFO4-tb/spectre/schematic/psf; Dataset: tran-tran

## X Virtuoso (R) Visualization &amp; Analysis XL

File Edit View Graph Axis Trace Marker Measurements Tools Window Browser Help

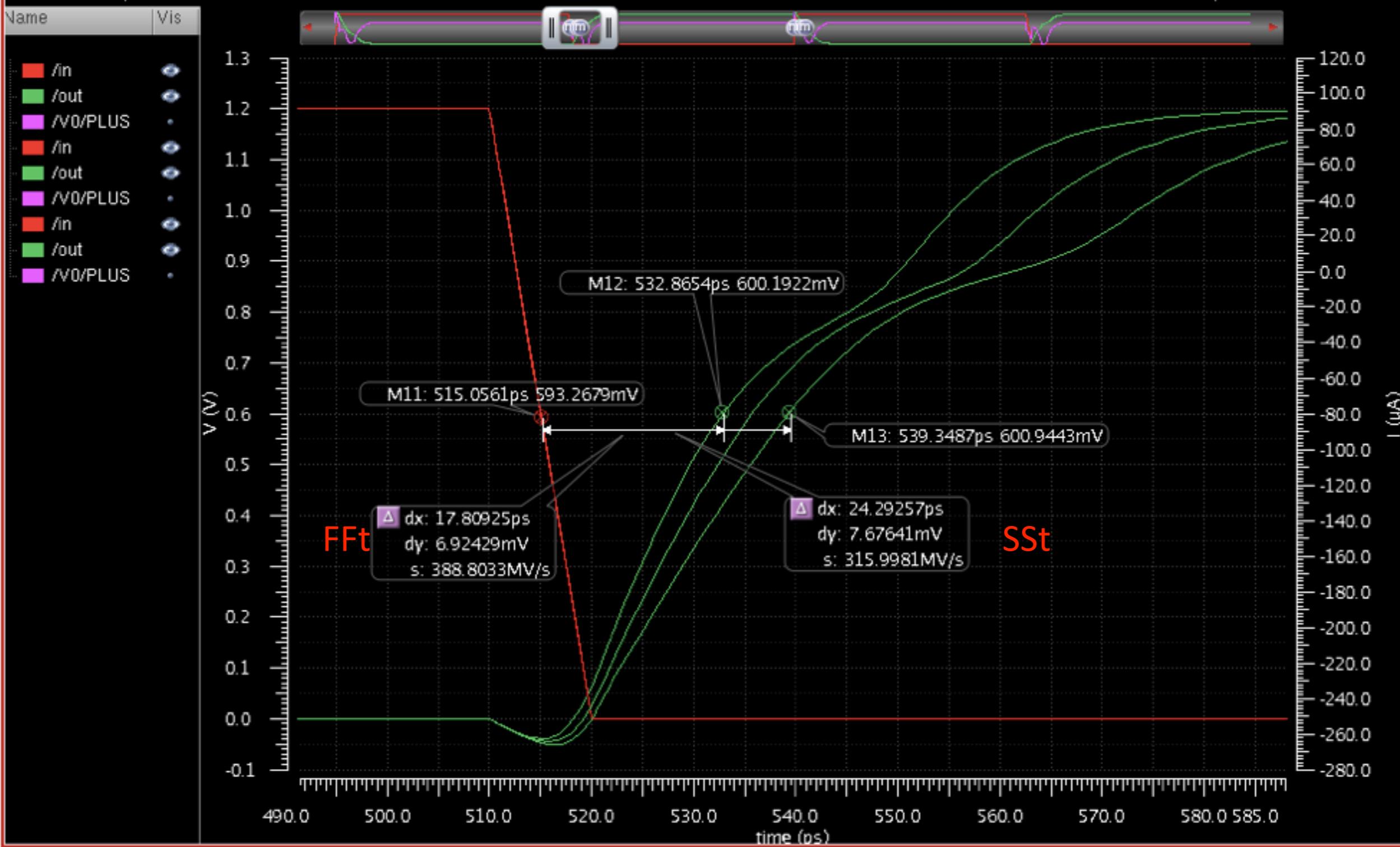
cadence



lab1 invFO4-tb schematic

## Transient Response

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mouse L:

M:

R:

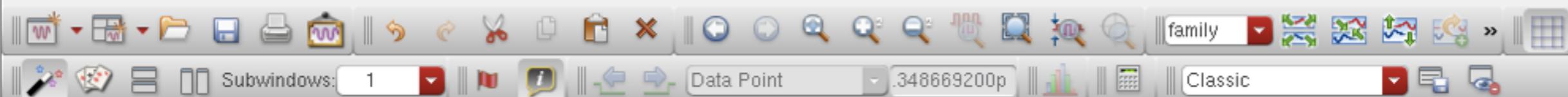
# Does it compute?

$L=60$ nm, $W=1$ $\mu$ m	SS corner	TT corner	FF corner	
$I_{DSAT,N}$	500	600	800	$\mu$ A/ $\mu$ m
$I_{DSAT,P}$	250	300	400	$\mu$ A/ $\mu$ m

How much slower is SS? -20 %

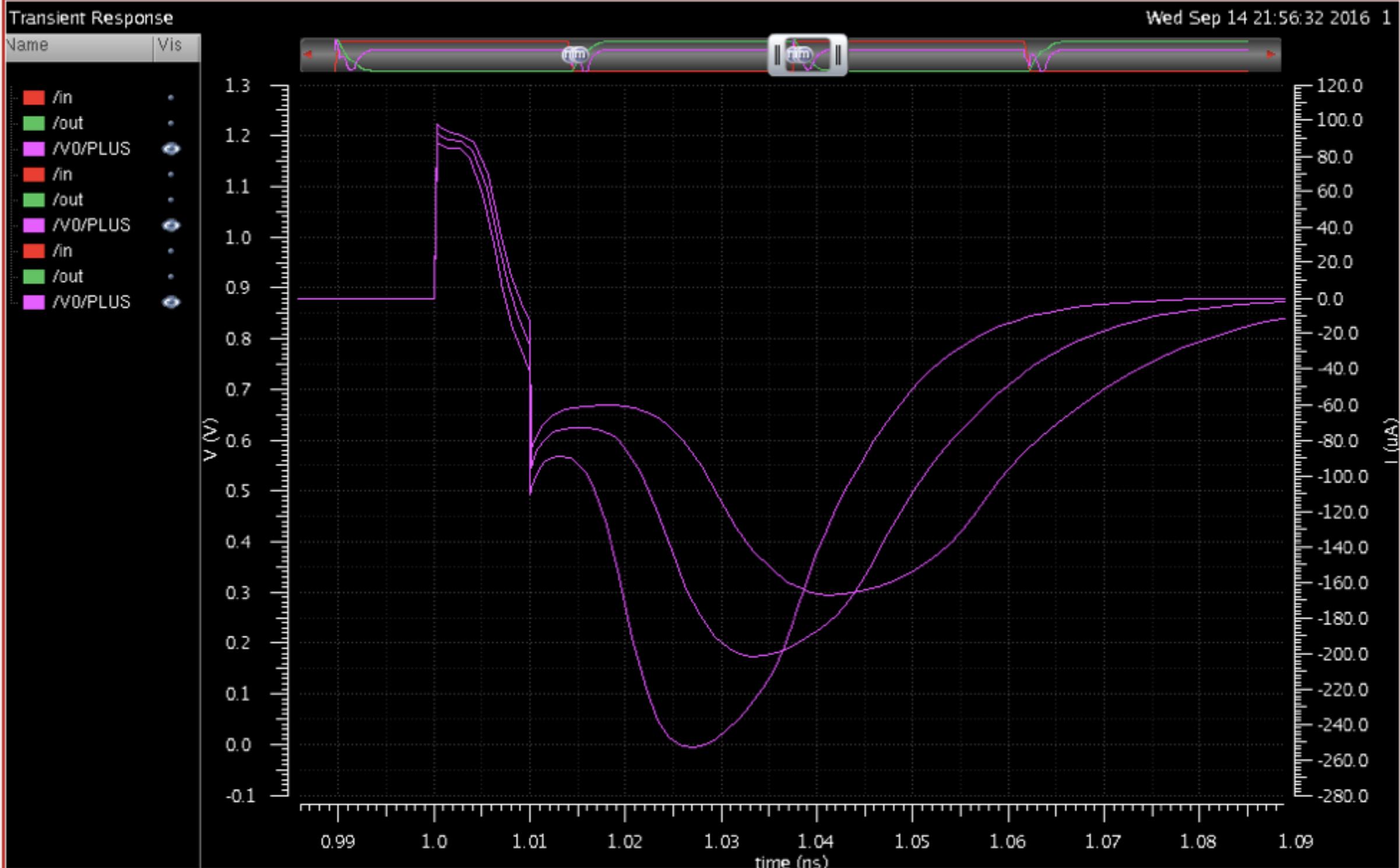
How much faster is FF? + 33%

If we assume the capacitances remain the same.



lab1 invFO4-tb schematic

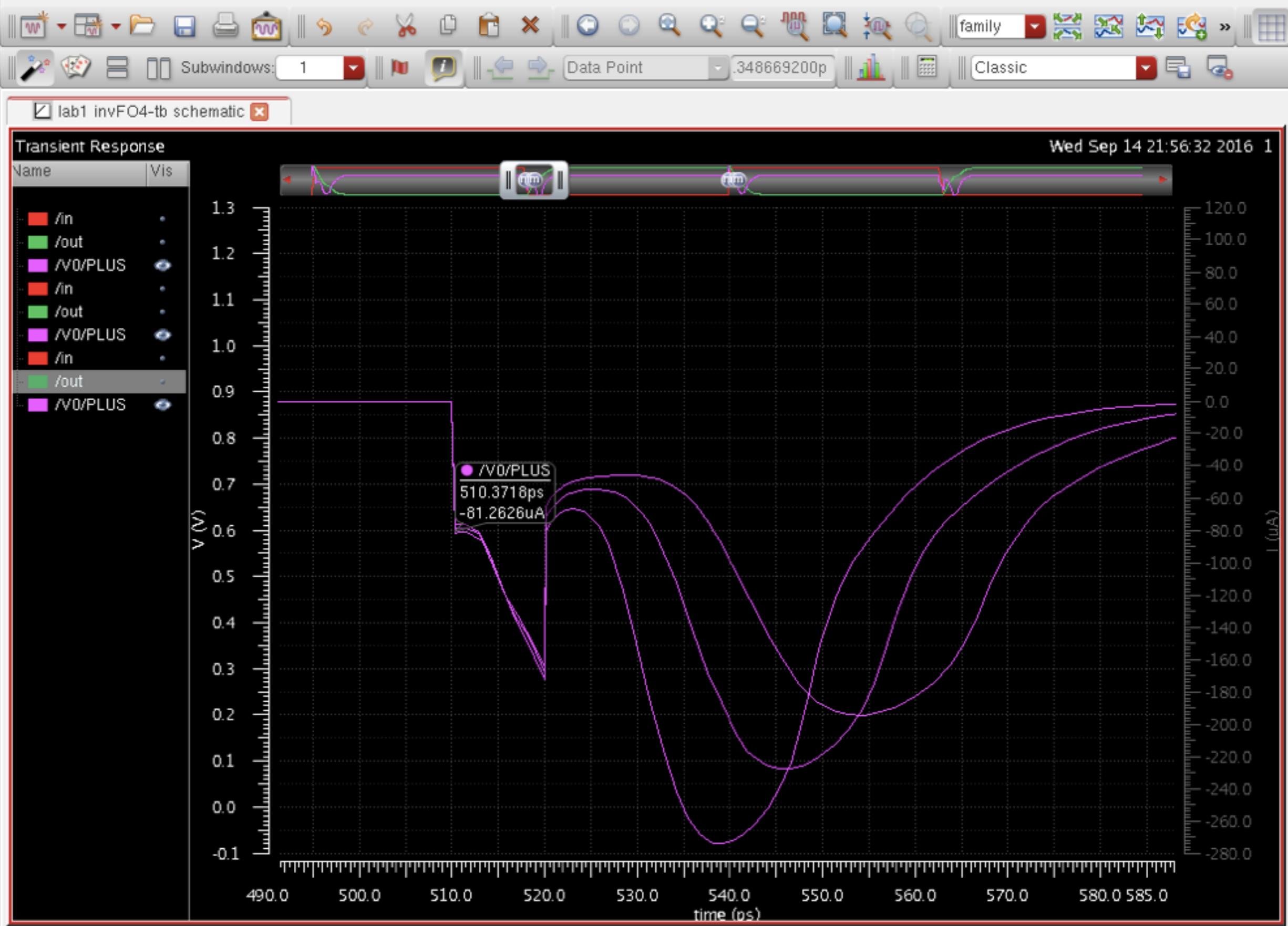
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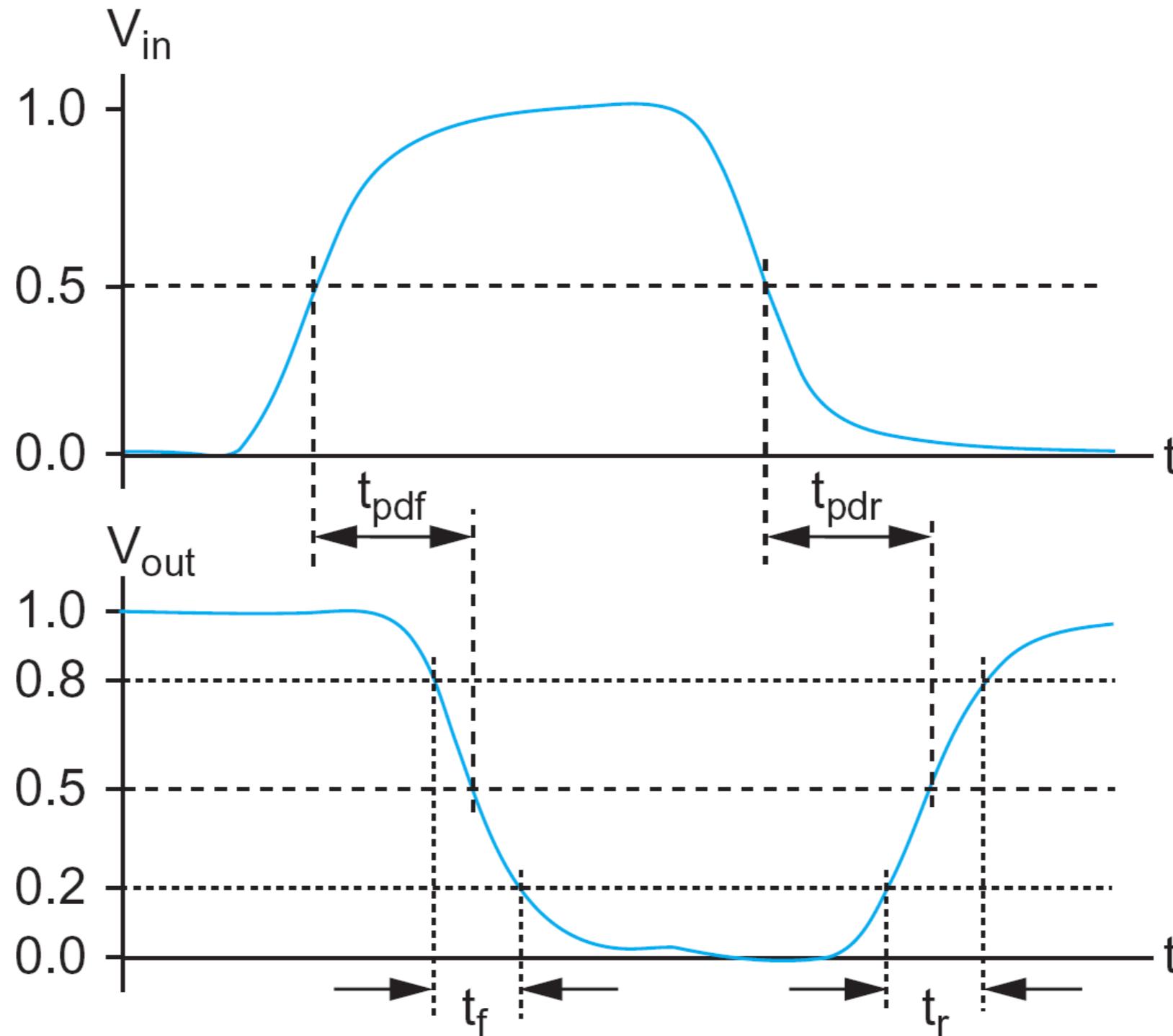
mouse L:

M:

R:

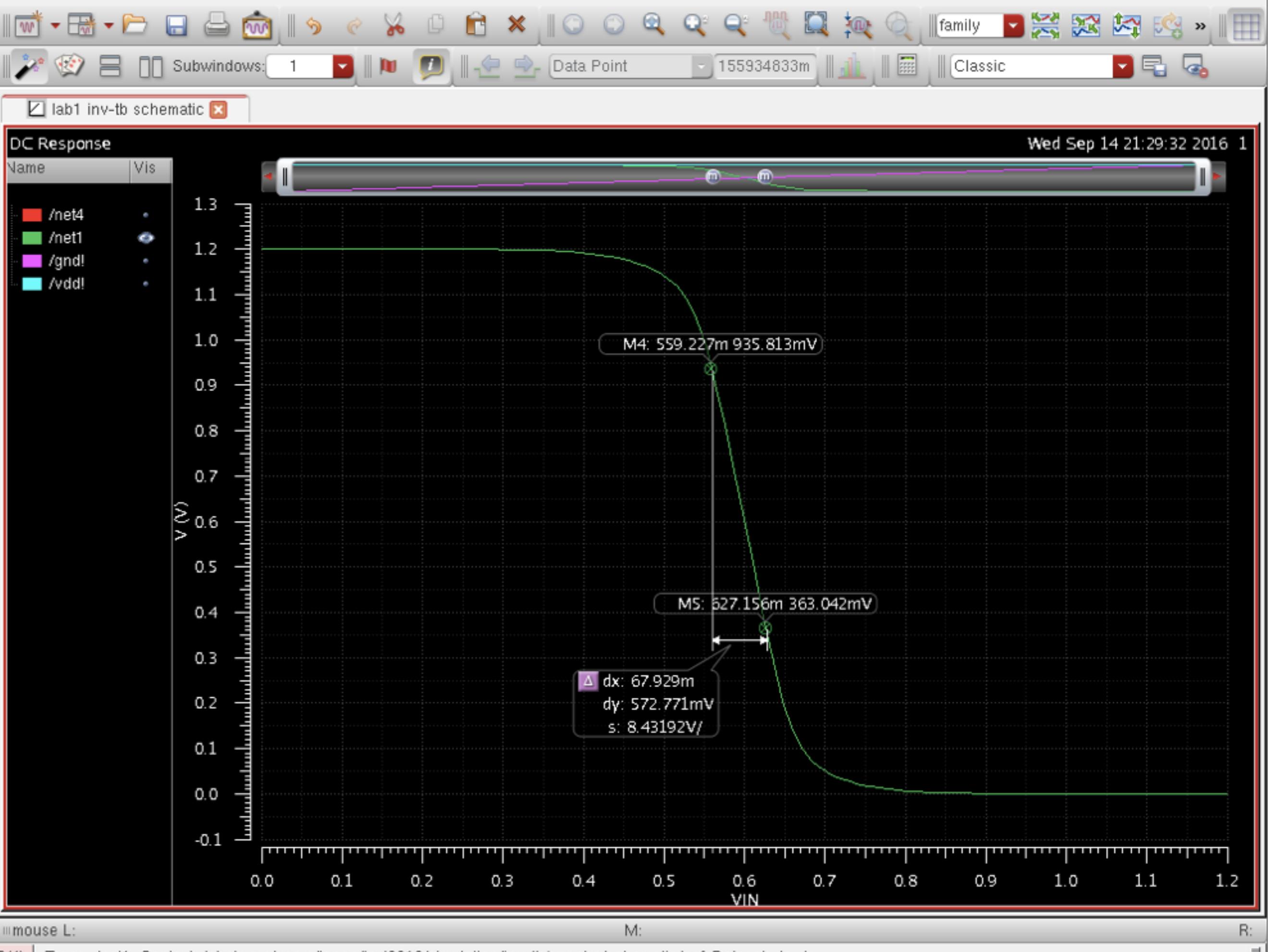


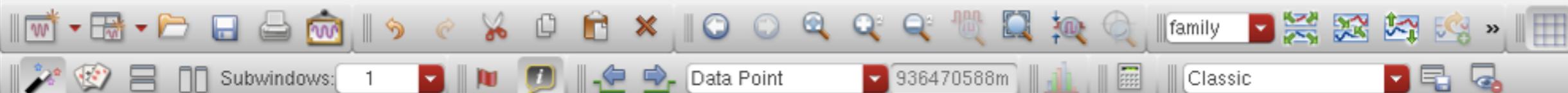
# Rise/fall time and delay



# Analysis types

- Transient analysis
  - In time, nonlinear and with capacitances
- DC analysis
  - No time, no capacitances (but still nonlinear)
  - Changes wrt some parameter, for example a source voltage



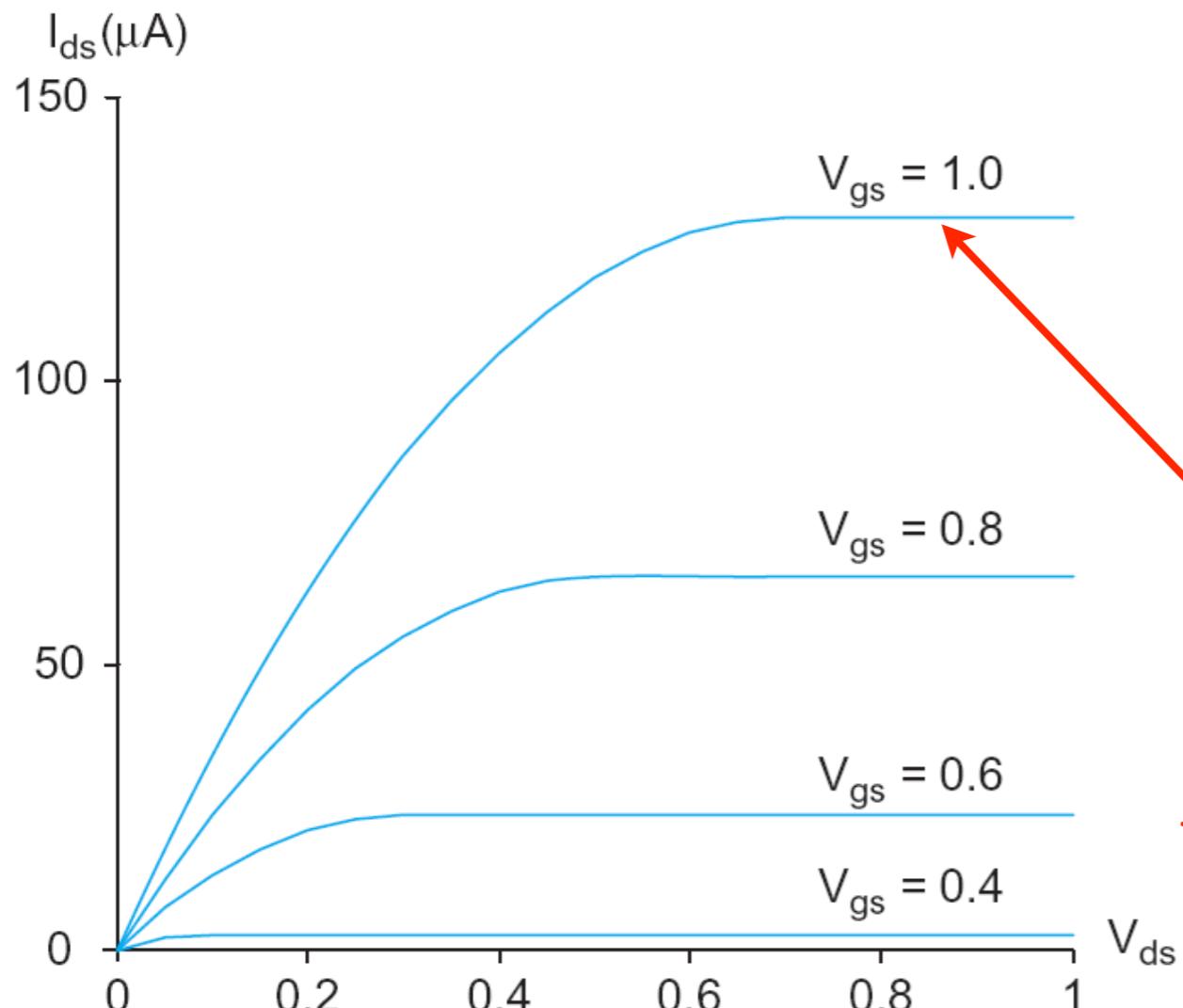


lab1 inv-tb schematic

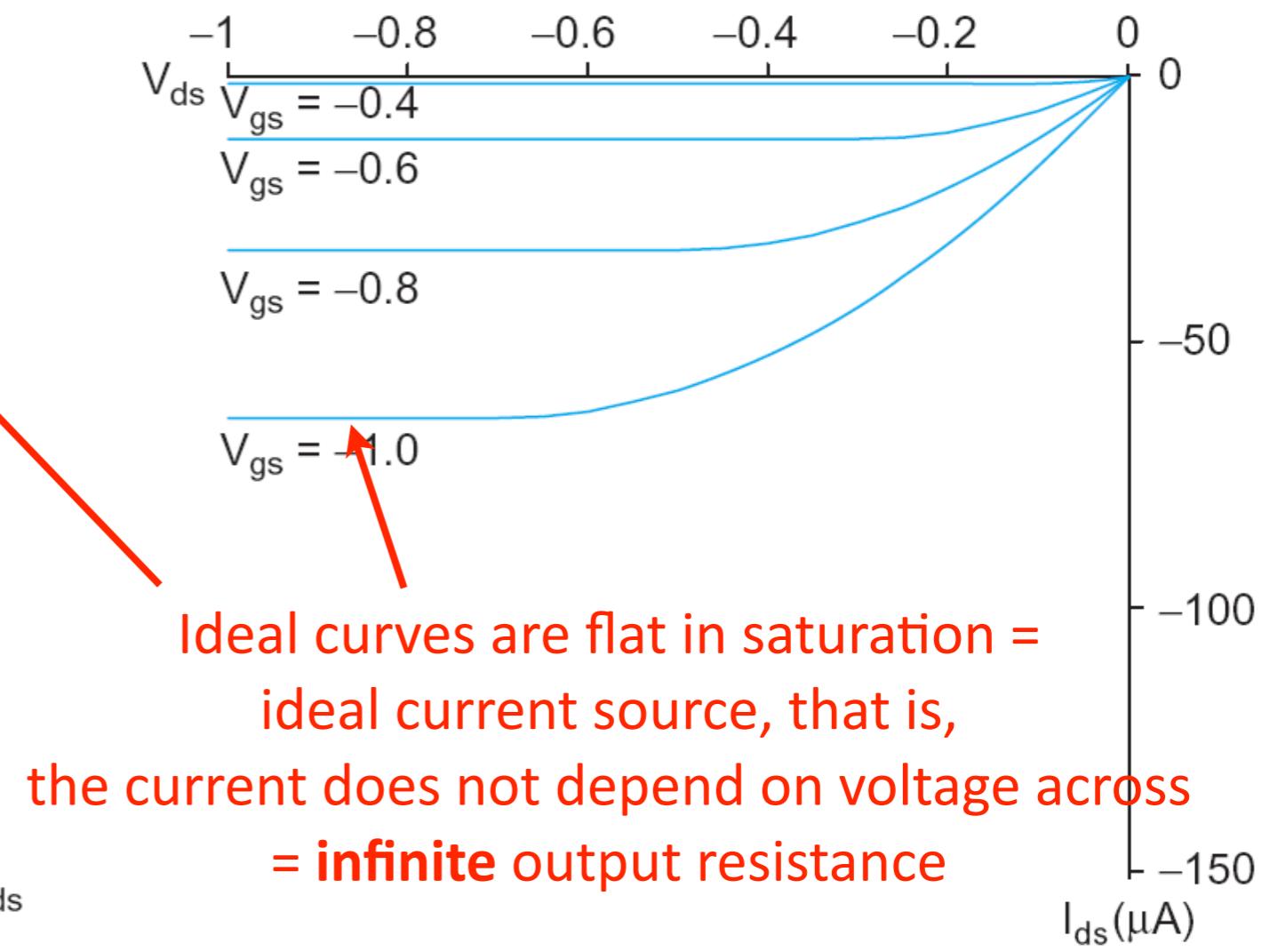
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# Ideal $I_{ds}$ curves



(a)



(b)

# Realistic $I_{ds}$ curves

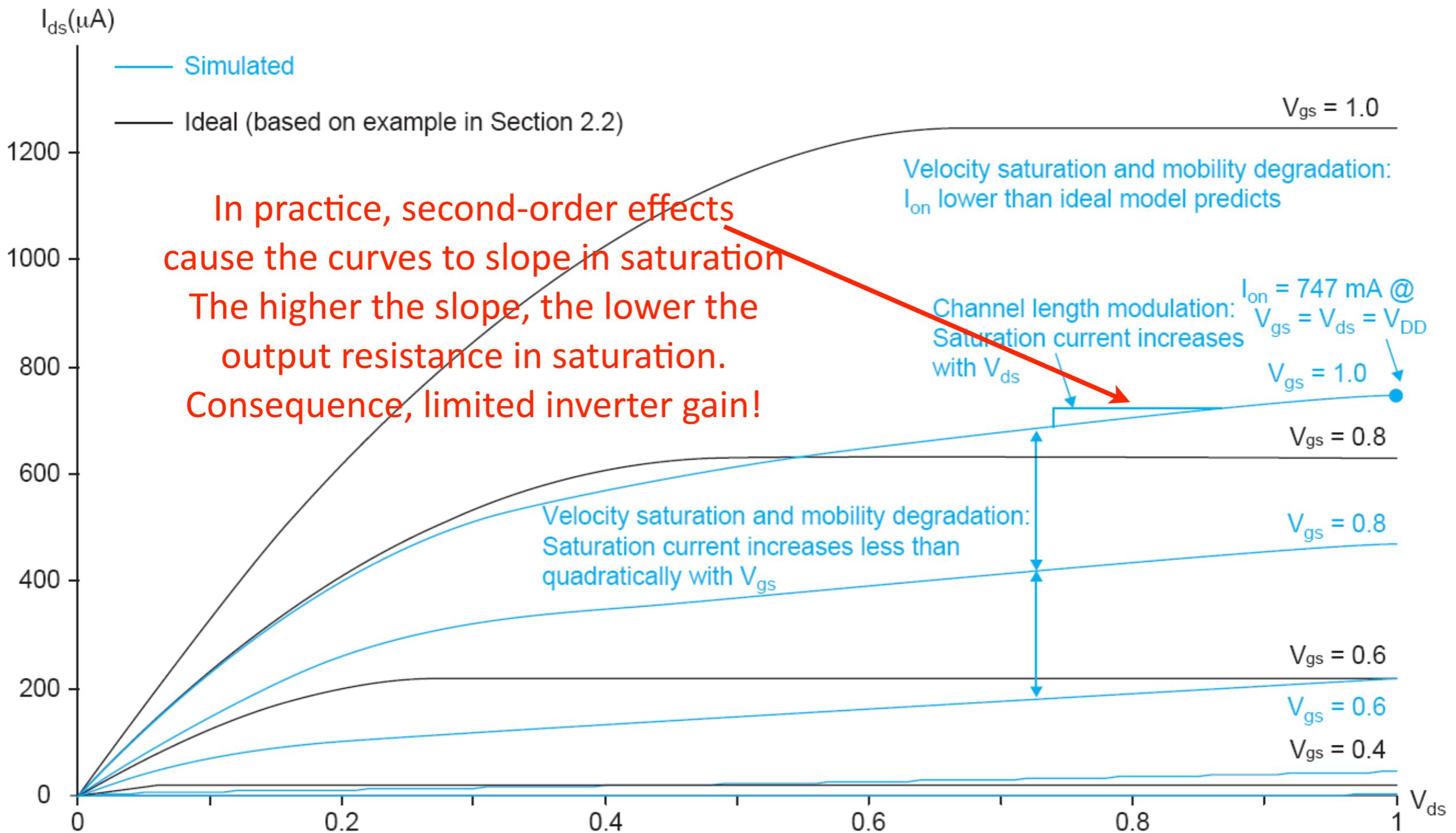


FIGURE 2.14 Simulated and ideal I-V characteristics